

IRGB4B60KD1PbF
IRGS4B60KD1PbF
IRGSL4B60KD1PbF

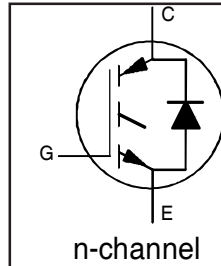
INSULATED GATE BIPOLAR TRANSISTOR WITH
ULTRAFAST SOFT RECOVERY DIODE

Features

- Low VCE (on) Non Punch Through IGBT Technology.
- 10µs Short Circuit Capability.
- Square RBSOA.
- Positive VCE (on) Temperature Coefficient.
- Maximum Junction Temperature rated at 175°C.
- Lead-Free

Benefits

- Benchmark Efficiency for Motor Control.
- Rugged Transient Performance.
- Low EMI.
- Excellent Current Sharing in Parallel Operation.

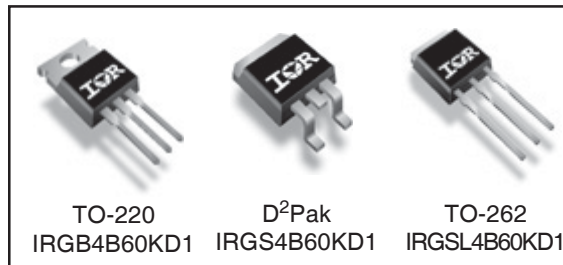


$$V_{CES} = 600V$$

$$I_C = 7.6A, T_C = 100^\circ C$$

$$t_{sc} > 10\mu s, T_J = 150^\circ C$$

$$V_{CE(on)} \text{ typ.} = 2.1V$$



Absolute Maximum Ratings

	Parameter	Max.	Units
V _{CES}	Collector-to-Emitter Voltage	600	V
I _C @ T _C = 25°C	Continuous Collector Current	11	A
I _C @ T _C = 100°C	Continuous Collector Current	7.6	
I _{CM}	Pulse Collector Current (Ref.Fig.C.T.5)	22	
I _{LM}	Clamped Inductive Load current ①	22	
I _F @ T _C = 25°C	Diode Continuous Forward Current	11	
I _F @ T _C = 100°C	Diode Continuous Forward Current	6.7	
I _{FM}	Diode Maximum Forward Current	22	
V _{GE}	Gate-to-Emitter Voltage	±20	V
P _D @ T _C = 25°C	Maximum Power Dissipation	63	W
P _D @ T _C = 100°C	Maximum Power Dissipation	31	
T _J	Operating Junction and	-55 to +175	°C
T _{STG}	Storage Temperature Range		
	Storage Temperature Range, for 10 sec.	300 (0.063 in. (1.6mm) from case)	

Thermal / Mechanical Characteristics

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case- IGBT	—	—	2.4	$^\circ C/W$
$R_{\theta JC}$	Junction-to-Case- Diode	—	—	6.1	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	—	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient	—	—	62	
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount, steady state)②	—	—	40	
Wt	Weight	—	1.44	—	g

IRGB/S/SL4B60KD1PbF

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	Ref.Fig.
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	$V_{GE} = 0V, I_C = 500\mu A$	
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.28	—	V/ $^\circ\text{C}$	$V_{GE} = 0V, I_C = 1mA (25^\circ\text{C}-150^\circ\text{C})$	
$V_{CE(on)}$	Collector-to-Emitter Voltage	—	2.1	2.5	V	$I_C = 4.0A, V_{GE} = 15V, T_J = 25^\circ\text{C}$	5,6,7
		—	2.5	2.8		$I_C = 4.0A, V_{GE} = 15V, T_J = 150^\circ\text{C}$	9,10,11
		—	2.6	2.9		$I_C = 4.0A, V_{GE} = 15V, T_J = 175^\circ\text{C}$	
$V_{GE(th)}$	Gate Threshold Voltage	3.5	4.5	5.5	V	$V_{CE} = V_{GE}, I_C = 250\mu A$	9,10,11
$\Delta V_{GE(th)}/\Delta T_J$	Threshold Voltage temp. coefficient	—	-8.1	—	mV/ $^\circ\text{C}$	$V_{CE} = V_{GE}, I_C = 1mA (25^\circ\text{C}-150^\circ\text{C})$	12
g_{fe}	Forward Transconductance	—	1.7	—	S	$V_{CE} = 50V, I_C = 4.0A, PW = 80\mu s$	
I_{CES}	Zero Gate Voltage Collector Current	—	1.0	150	μA	$V_{GE} = 0V, V_{CE} = 600V$	
		—	136	600		$V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$	
		—	722	2400		$V_{GE} = 0V, V_{CE} = 600V, T_J = 175^\circ\text{C}$	
V_{FM}	Diode Forward Voltage Drop	—	1.4	2.0	V	$I_F = 4.0A$	8
		—	1.3	1.8		$I_F = 4.0A, T_J = 150^\circ\text{C}$	
		—	1.2	1.7		$I_F = 4.0A, T_J = 175^\circ\text{C}$	
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$	

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	Ref.Fig.
Q_g	Total Gate Charge (turn-on)	—	12	—	nC	$I_C = 4.0A$	23
Q_{ge}	Gate-to-Emitter Charge (turn-on)	—	1.7	—		$V_{CC} = 400V$	CT1
Q_{gc}	Gate-to-Collector Charge (turn-on)	—	6.5	—		$V_{GE} = 15V$	
E_{on}	Turn-On Switching Loss	—	73	80	μJ	$I_C = 4.0A, V_{CC} = 400V$	CT4
E_{off}	Turn-Off Switching Loss	—	47	53		$V_{GE} = 15V, R_G = 100\Omega, L = 2.5mH$	
E_{tot}	Total Switching Loss	—	120	130		$T_J = 25^\circ\text{C} \text{ ③}$	
$t_{d(on)}$	Turn-On delay time	—	22	28	ns	$I_C = 4.0A, V_{CC} = 400V$	CT4
t_r	Rise time	—	18	23		$V_{GE} = 15V, R_G = 100\Omega, L = 2.5mH$	
$t_{d(off)}$	Turn-Off delay time	—	100	110		$T_J = 25^\circ\text{C}$	
t_f	Fall time	—	66	80	μJ	$I_C = 4.0A, V_{CC} = 400V$	CT4
E_{on}	Turn-On Switching Loss	—	130	150		$V_{GE} = 15V, R_G = 100\Omega, L = 2.5mH$	13,15
E_{off}	Turn-Off Switching Loss	—	83	140		$T_J = 150^\circ\text{C} \text{ ③}$	WF1,WF2
E_{tot}	Total Switching Loss	—	220	280	ns	$I_C = 4.0A, V_{CC} = 400V$	14,16
$t_{d(on)}$	Turn-On delay time	—	22	27		$V_{GE} = 15V, R_G = 100\Omega, L = 2.5mH$	CT4
t_r	Rise time	—	18	22		$T_J = 150^\circ\text{C}$	WF1
$t_{d(off)}$	Turn-Off delay time	—	120	130	pF		WF2
t_f	Fall time	—	79	89			
C_{ies}	Input Capacitance	—	190	—		$V_{GE} = 0V$	22
C_{oes}	Output Capacitance	—	25	—	pF	$V_{CC} = 30V$	
C_{res}	Reverse Transfer Capacitance	—	6.2	—		$f = 1.0MHz$	
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				$T_J = 150^\circ\text{C}, I_C = 22A, V_p = 600V$ $V_{CC}=500V, V_{GE} = +15V \text{ to } 0V, R_G = 100\Omega$	4 CT2
SCSOA	Short Circuit Safe Operating Area	10	—	—	μs	$T_J = 150^\circ\text{C}, V_p = 600V, R_G = 100\Omega$ $V_{CC}=360V, V_{GE} = +15V \text{ to } 0V$	CT3 WF4
E_{rec}	Reverse Recovery Energy of the Diode	—	81	100	μJ	$T_J = 150^\circ\text{C}$	17,18,19
t_{rr}	Diode Reverse Recovery Time	—	93	—	ns	$V_{CC} = 400V, I_F = 4.0A, L = 2.5mH$	20,21
I_{rr}	Peak Reverse Recovery Current	—	6.3	7.9	A	$V_{GE} = 15V, R_G = 100\Omega$	CT4,WF3

Note ① to ③ are on page 16

IRGB/S/SL4B60KD1PbF

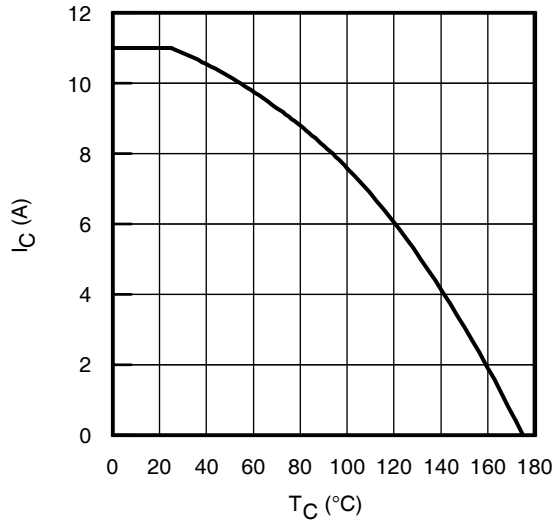


Fig. 1 - Maximum DC Collector Current vs. Case Temperature

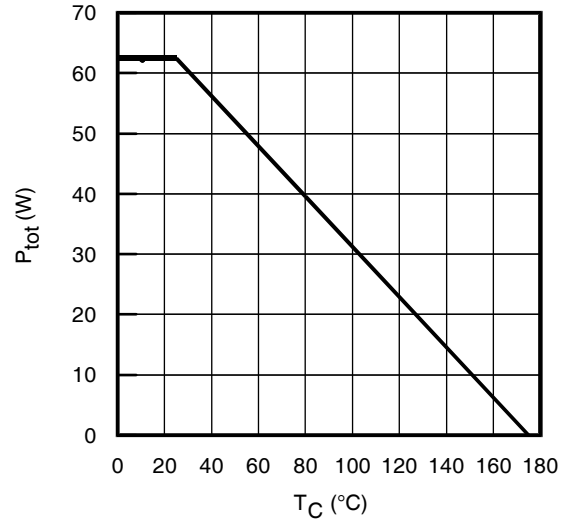


Fig. 2 - Power Dissipation vs. Case Temperature

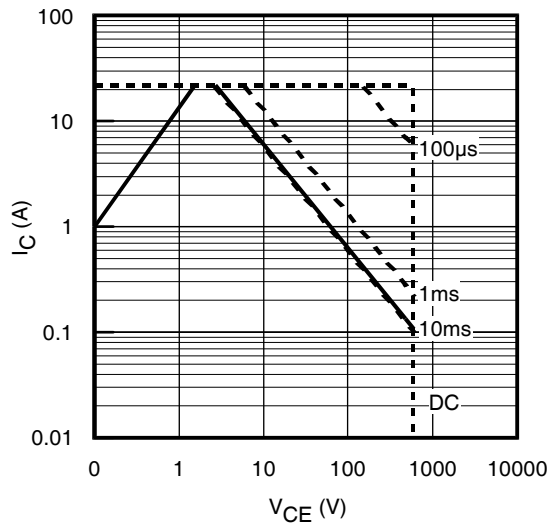


Fig. 3 - Forward SOA
 $T_C = 25^\circ\text{C}$; $T_J \leq 150^\circ\text{C}$

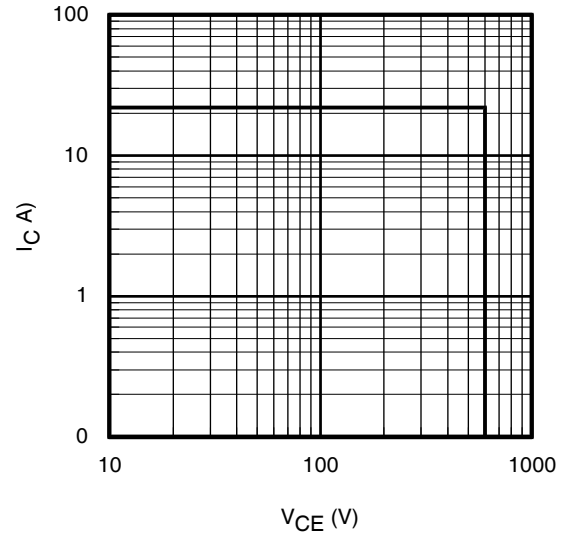


Fig. 4 - Reverse Bias SOA
 $T_J = 150^\circ\text{C}$; $V_{GE} = 15\text{V}$

IRGB/S/SL4B60KD1PbF

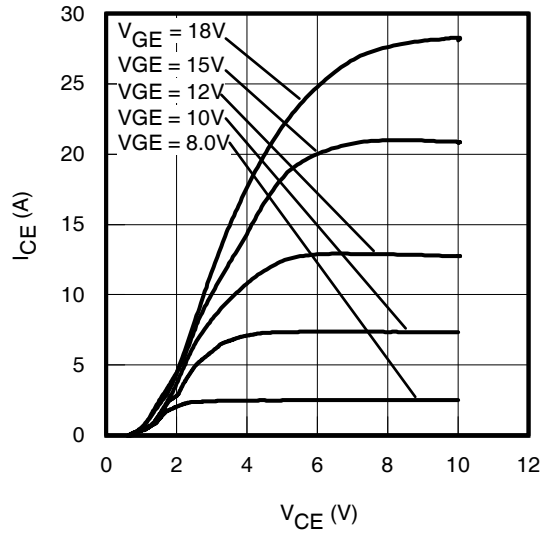


Fig. 5 - Typ. IGBT Output Characteristics
 $T_J = -40^\circ\text{C}$; $t_p = 80\mu\text{s}$

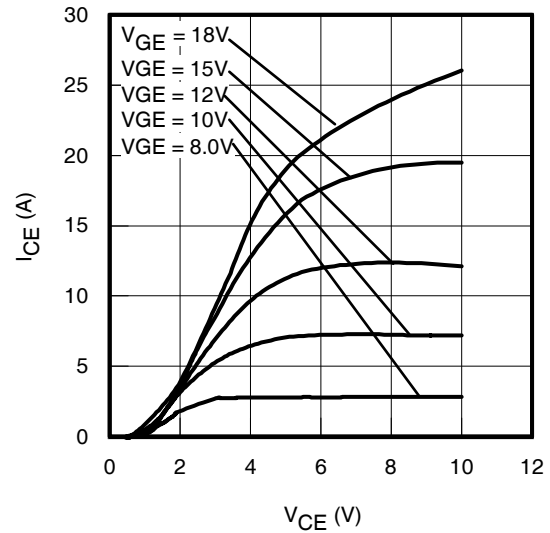


Fig. 6 - Typ. IGBT Output Characteristics
 $T_J = 25^\circ\text{C}$; $t_p = 80\mu\text{s}$

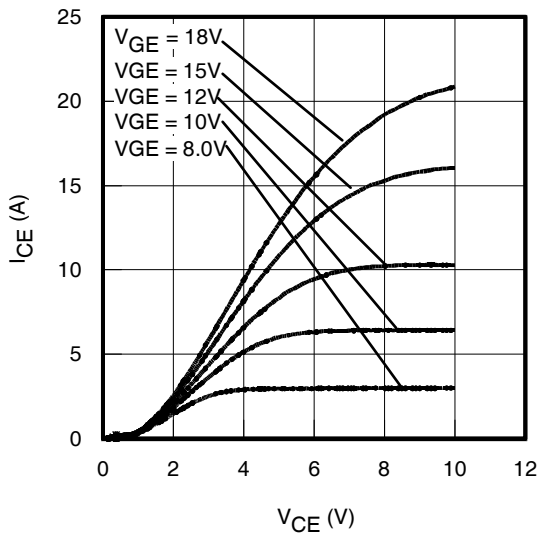


Fig. 7 - Typ. IGBT Output Characteristics
 $T_J = 150^\circ\text{C}$; $t_p = 80\mu\text{s}$

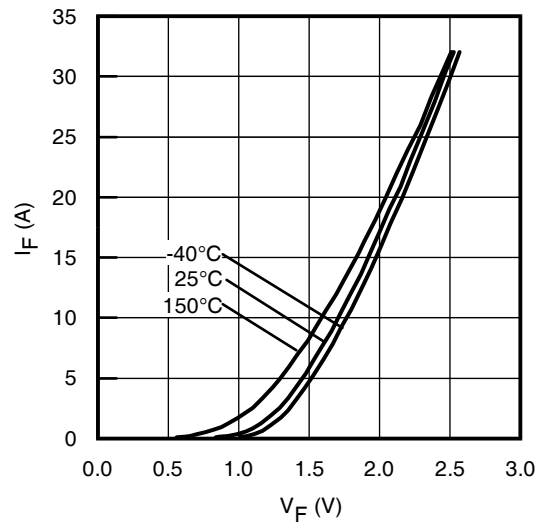


Fig. 8 - Typ. Diode Forward Characteristics
 $t_p = 80\mu\text{s}$

IRGB/S/SL4B60KD1PbF

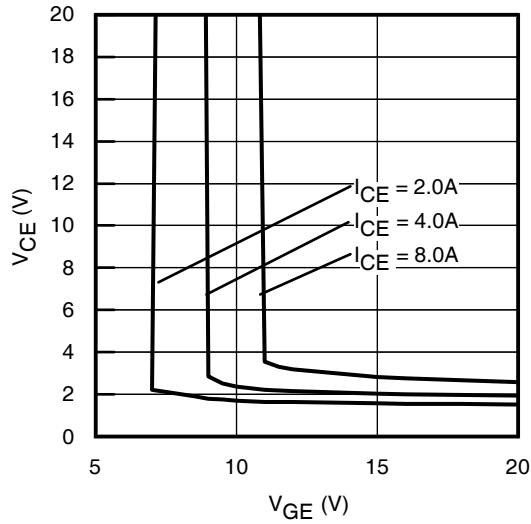


Fig. 9 - Typical V_{CE} vs. V_{GE}
 $T_J = -40^{\circ}\text{C}$

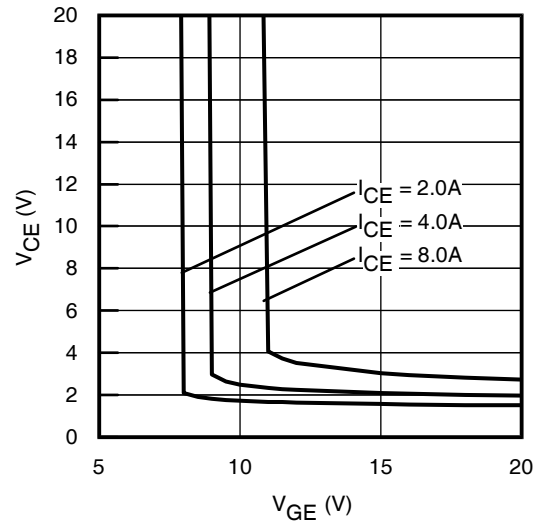


Fig. 10 - Typical V_{CE} vs. V_{GE}
 $T_J = 25^{\circ}\text{C}$

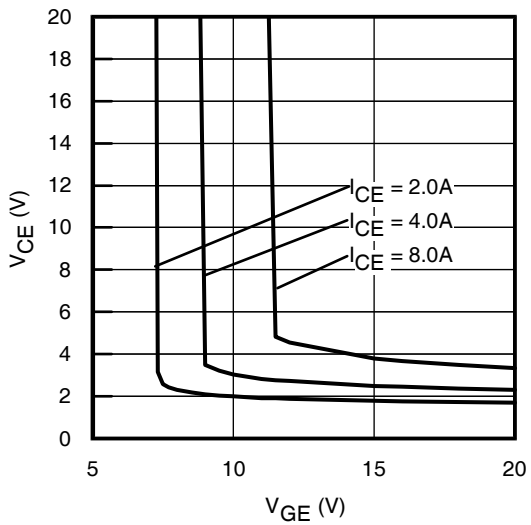


Fig. 11 - Typical V_{CE} vs. V_{GE}
 $T_J = 150^{\circ}\text{C}$

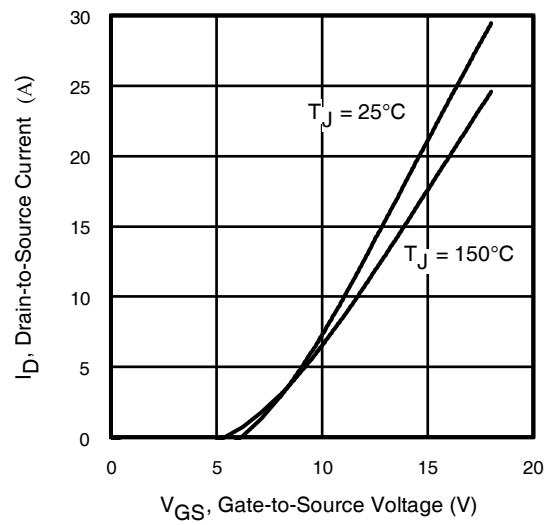


Fig. 12 - Typ. Transfer Characteristics
 $V_{CE} = 360\text{V}$; $t_p = 10\mu\text{s}$

IRGB/S/SL4B60KD1PbF

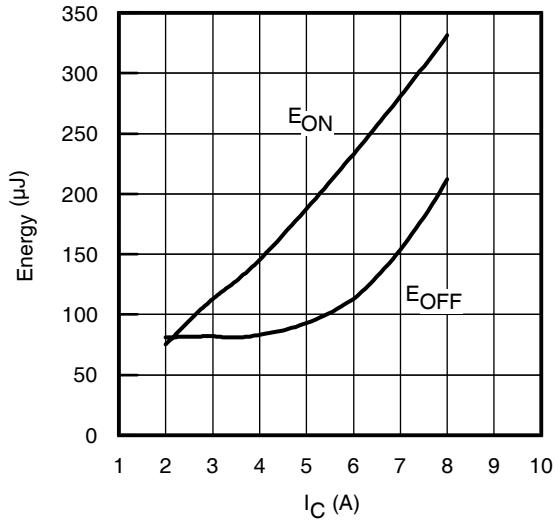


Fig. 13 - Typ. Energy Loss vs. I_C
 $T_J = 150^\circ\text{C}$; $L=2.5\text{mH}$; $V_{CE}= 400\text{V}$,
 $R_G= 100\Omega$; $V_{GE}= 15\text{V}$

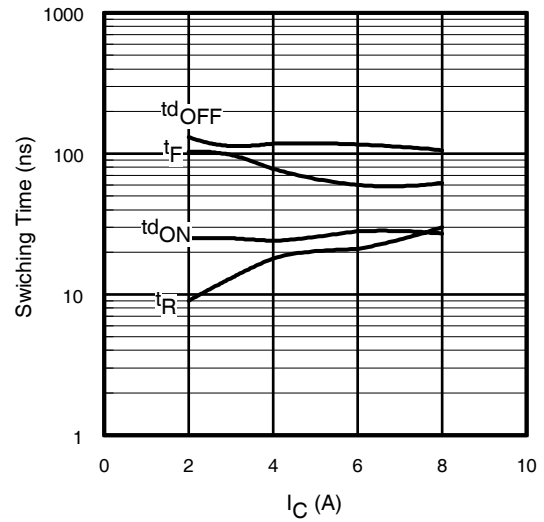


Fig. 14 - Typ. Switching Time vs. I_C
 $T_J = 150^\circ\text{C}$; $L=2.5\text{mH}$; $V_{CE}= 400\text{V}$
 $R_G= 100\Omega$; $V_{GE}= 15\text{V}$

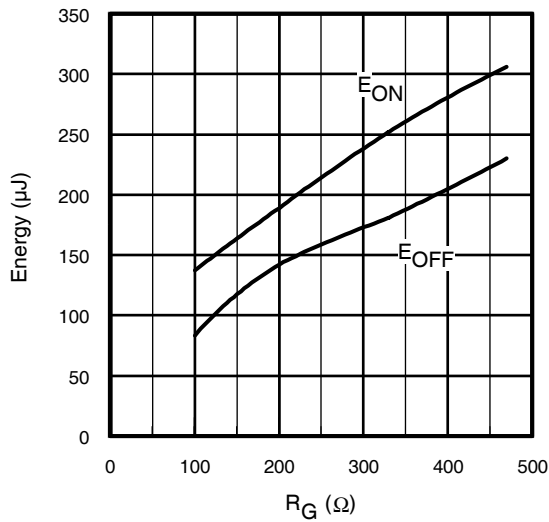


Fig. 15 - Typ. Energy Loss vs. R_G
 $T_J = 150^\circ\text{C}$; $L=2.5\text{mH}$; $V_{CE}= 400\text{V}$
 $I_{CE}= 4.0\text{A}$; $V_{GE}= 15\text{V}$

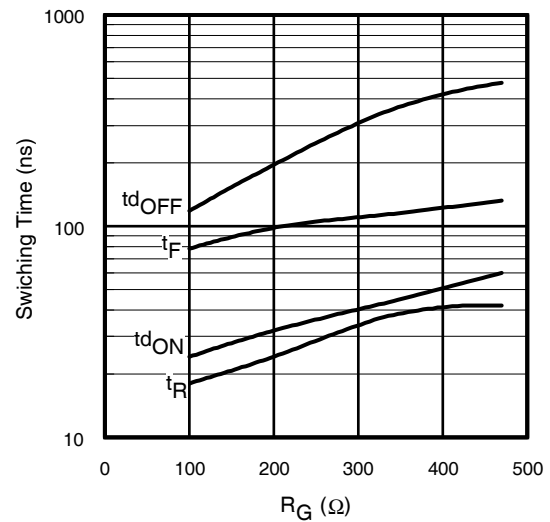


Fig. 16 - Typ. Switching Time vs. R_G
 $T_J = 150^\circ\text{C}$; $L=2.5\text{mH}$; $V_{CE}= 400\text{V}$
 $I_{CE}= 4.0\text{A}$; $V_{GE}= 15\text{V}$

IRGB/S/SL4B60KD1PbF

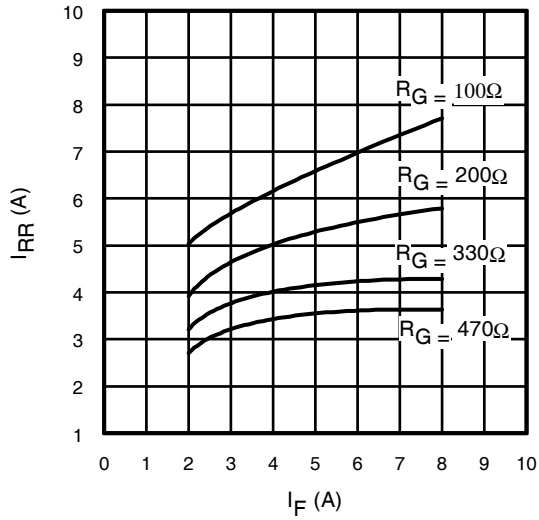


Fig. 17 - Typical Diode I_{RR} vs. I_F
 $T_J = 150^\circ\text{C}$

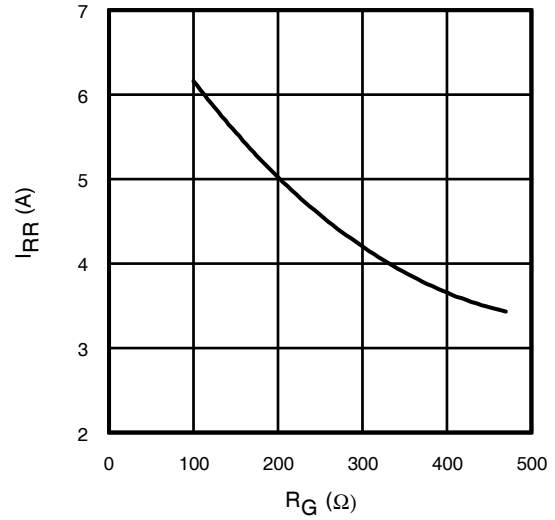


Fig. 18 - Typical Diode I_{RR} vs. R_G
 $T_J = 150^\circ\text{C}$; $I_F = 4.0\text{A}$

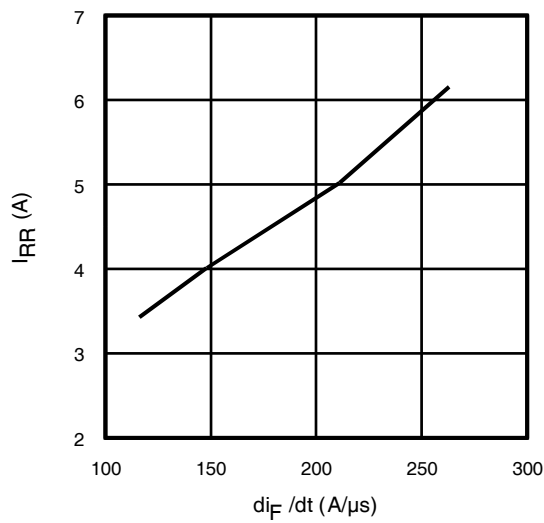


Fig. 19- Typical Diode I_{RR} vs. di_F/dt
 $V_{CC} = 400\text{V}$; $V_{GE} = 15\text{V}$;
 $I_F = 4.0\text{A}$; $T_J = 150^\circ\text{C}$

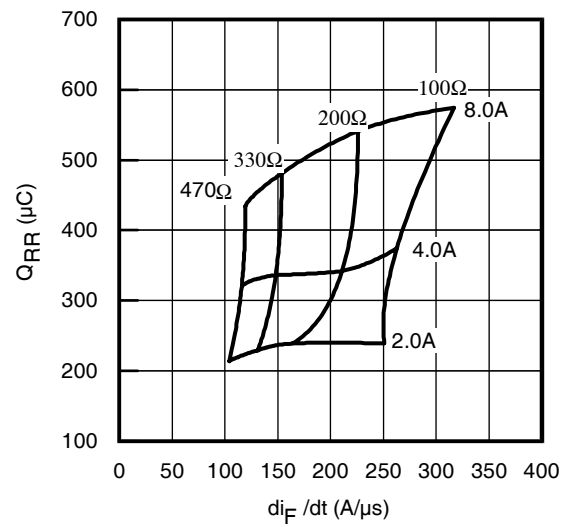


Fig. 20 - Typical Diode Q_{RR}
 $V_{CC} = 400\text{V}$; $V_{GE} = 15\text{V}$; $T_J = 150^\circ\text{C}$

IRGB/S/SL4B60KD1PbF

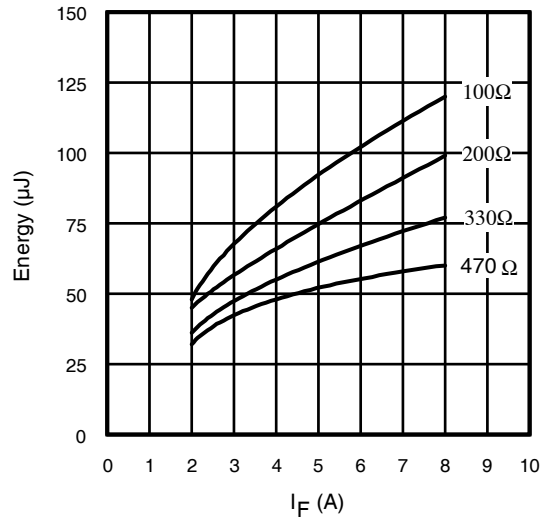


Fig. 21 - Typical Diode E_{RR} vs. I_F
 $T_J = 150^\circ\text{C}$

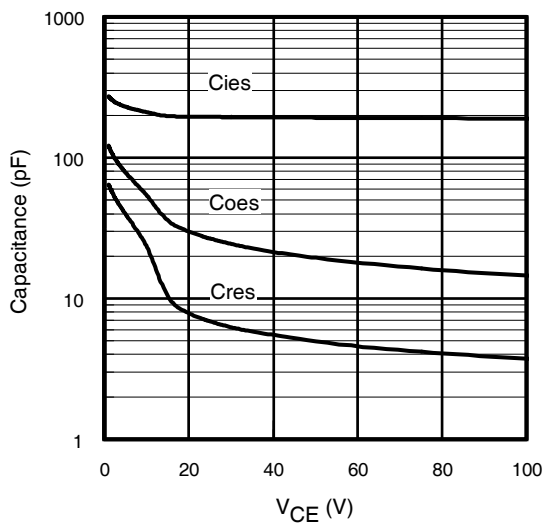


Fig. 22- Typ. Capacitance vs. V_{CE}
 $V_{GE} = 0\text{V}$; $f = 1\text{MHz}$

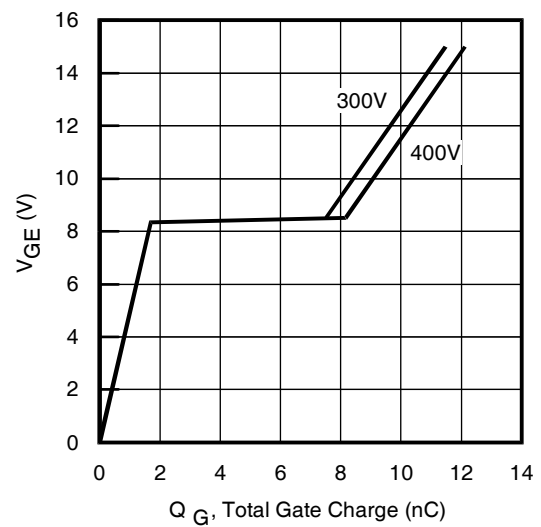


Fig. 23 - Typical Gate Charge vs. V_{GE}
 $I_{CE} = 4.0\text{A}$; $L = 3150\mu\text{H}$

IRGB/S/SL4B60KD1PbF

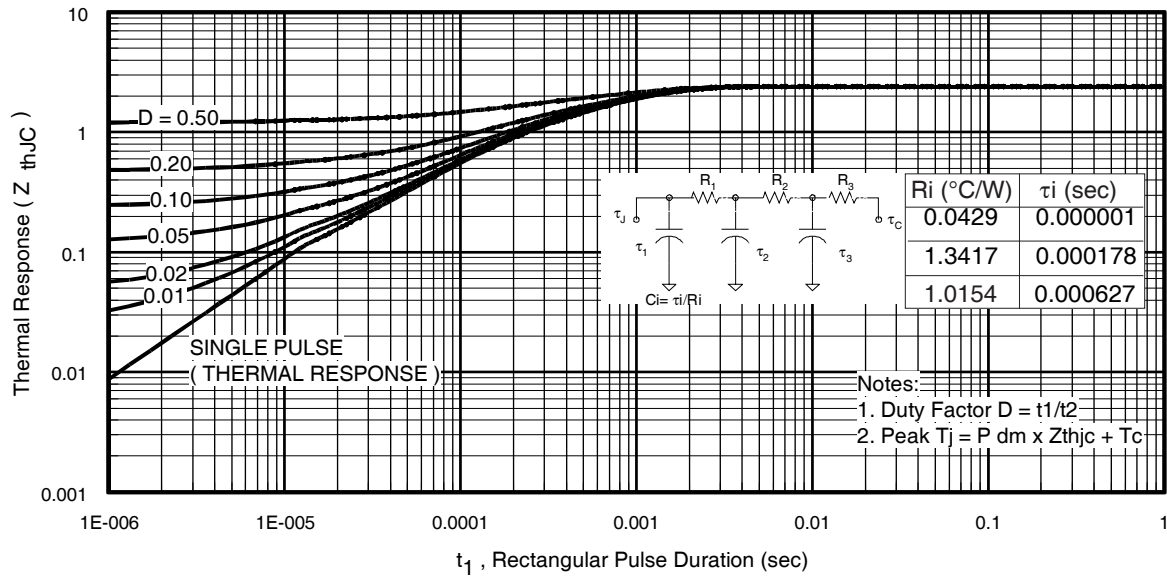


Fig 24. Maximum Transient Thermal Impedance, Junction-to-Case (IGBT)

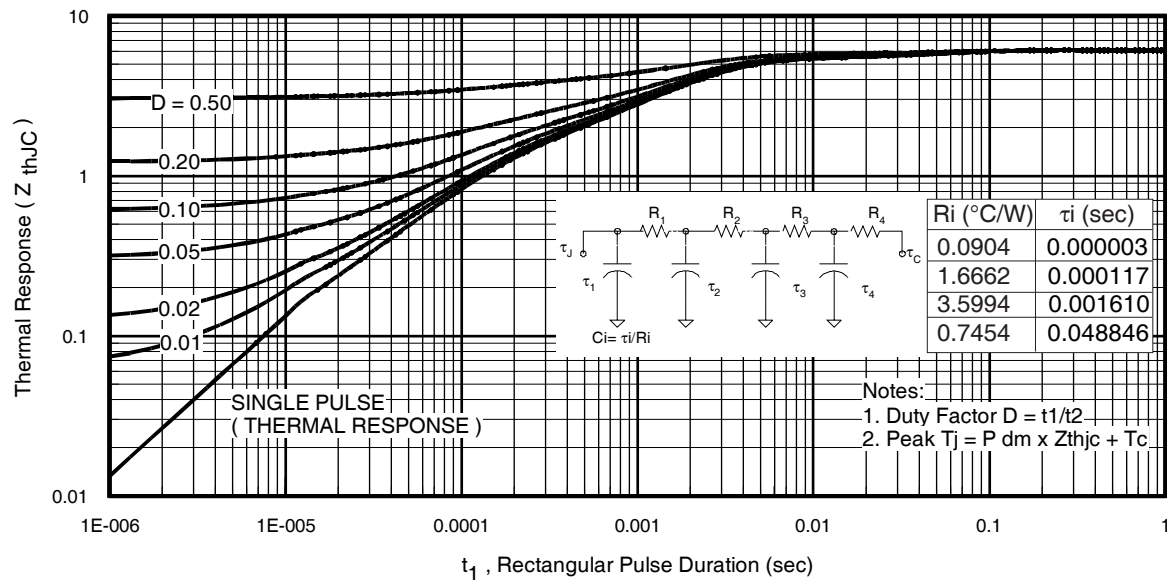


Fig 25. Maximum Transient Thermal Impedance, Junction-to-Case (DIODE)

IRGB/S/SL4B60KD1PbF

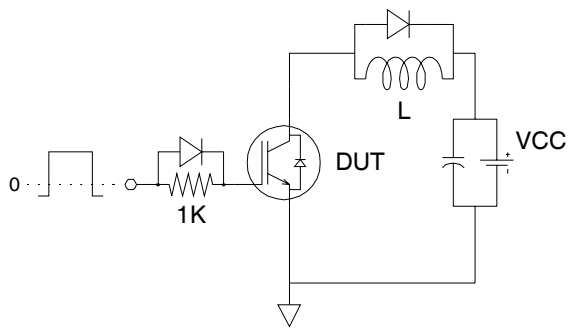


Fig.C.T.1 - Gate Charge Circuit (turn-off)

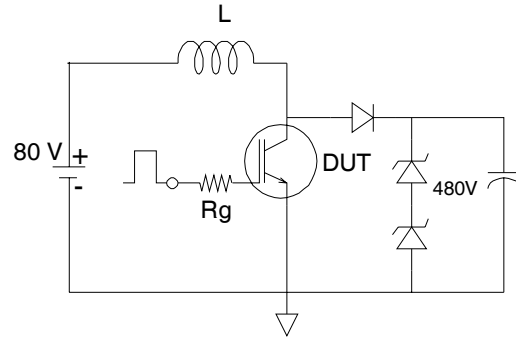


Fig.C.T.2 - RBSOA Circuit

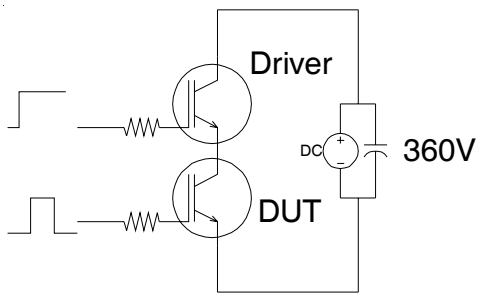


Fig.C.T.3 - S.C.SOA Circuit

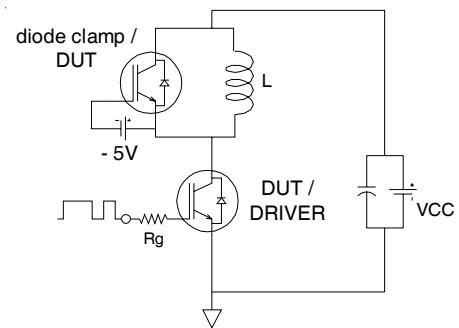


Fig.C.T.4 - Switching Loss Circuit

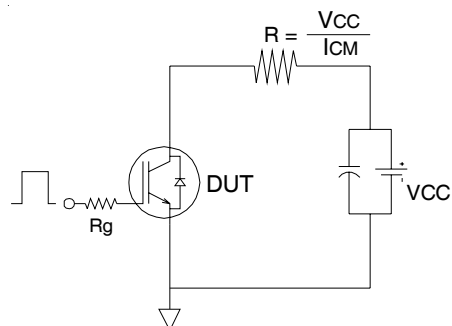


Fig.C.T.5 - Resistive Load Circuit

IRGB/S/SL4B60KD1PbF

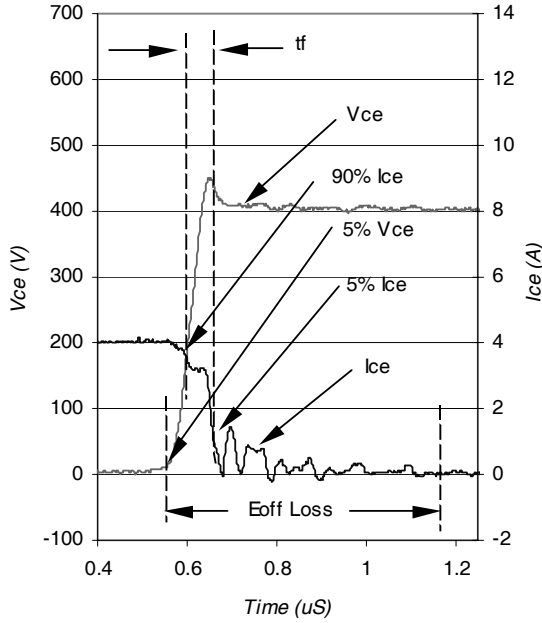


Fig. WF1- Typ. Turn-off Loss Waveform
@ $T_J = 150^{\circ}\text{C}$ using Fig. CT.4

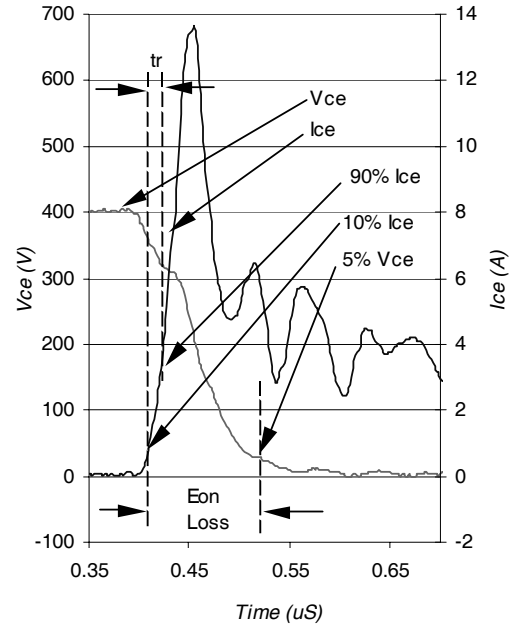


Fig. WF2- Typ. Turn-on Loss Waveform
@ $T_J = 150^{\circ}\text{C}$ using Fig. CT.4

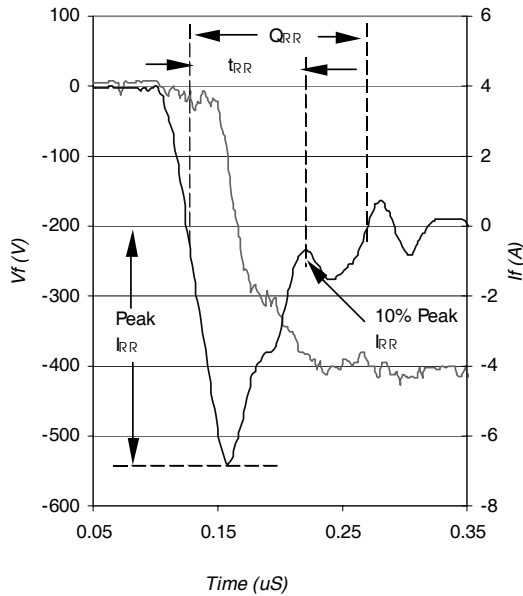


Fig. WF3- Typ. Diode Recovery Waveform
@ $T_J = 150^{\circ}\text{C}$ using Fig. CT.4

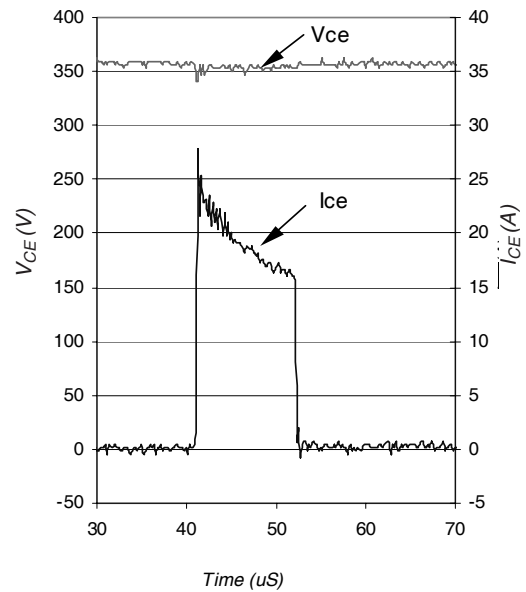
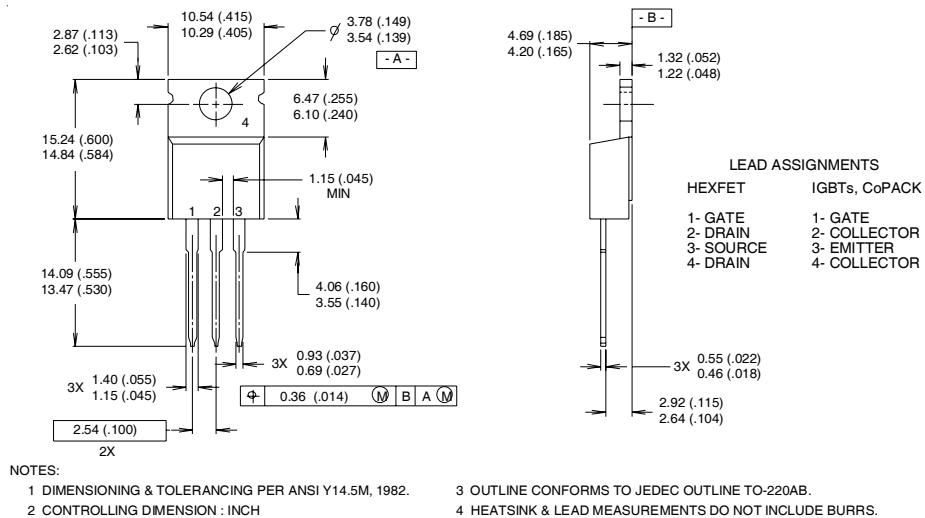


Fig. WF4- Typ. S.C Waveform
@ $T_C = 150^{\circ}\text{C}$ using Fig. CT.3

IRGB/S/SL4B60KD1PbF

TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



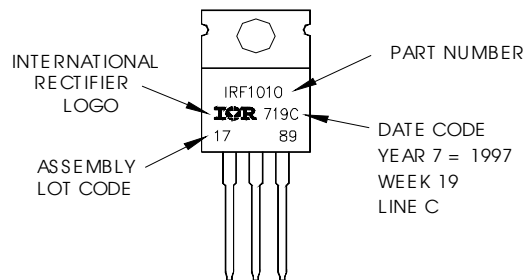
TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010

LOT CODE 1789

ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"

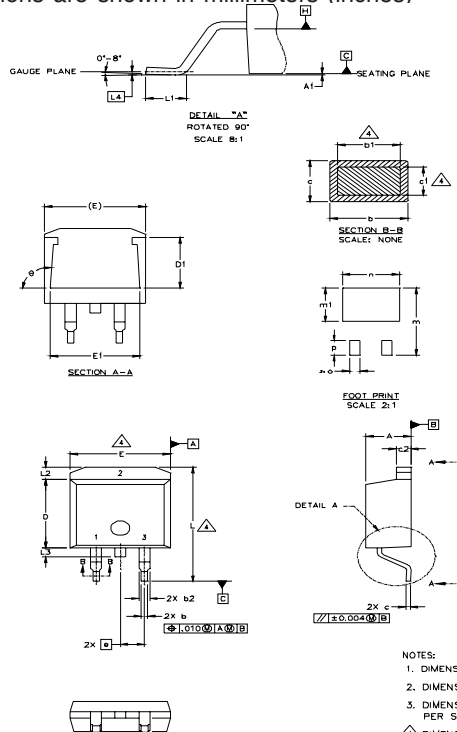
Note: "P" in assembly line
position indicates "Lead-Free"



IRGB/S/SL4B60KD1PbF

D²Pak Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	4
A1		0.127		.005	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	
b2	1.14	1.40	.045	.055	4
c	0.43	0.63	.017	.025	
c1	0.38	0.74	.015	.029	
c2	1.14	1.40	.045	.055	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	14.61	15.88	.575	.625	
L1	1.78	2.79	.070	.110	
L2		1.65		.065	
L3	1.27	1.78	.050	.070	
L4	0.25 BSC		.010 BSC		
m	17.78		.700		
m1	8.89		.350		
n	11.43		.450		
o	2.08		.082		
p	3.81		.150		
θ	90°	93°	90°	93°	

LEAD ASSIGNMENTS

HEXFET	IGBTs, CoPACK	DIODES
1- GATE	1- GATE	1- ANODE *
2- DRAIN	2- COLLECTOR	2- CATHODE
3- SOURCE	3- EMITTER	3- ANODE

* PART DEPENDENT.

NOTES:

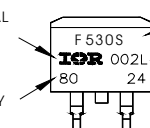
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 (.005") PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

D²Pak Part Marking Information (Lead-Free)

EXAMPLE: THIS IS AN IRF530S WITH
LOT CODE 8024
ASSEMBLED ON WW 02, 2000
IN THE ASSEMBLY LINE "L"

Note: "P" in assembly line
position indicates "Lead-Free"

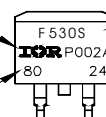
INTERNATIONAL
RECTIFIER
LOGO
ASSEMBLY
LOT CODE



PART NUMBER
DATE CODE
YEAR 0 = 2000
WEEK 02
LINE L

OR

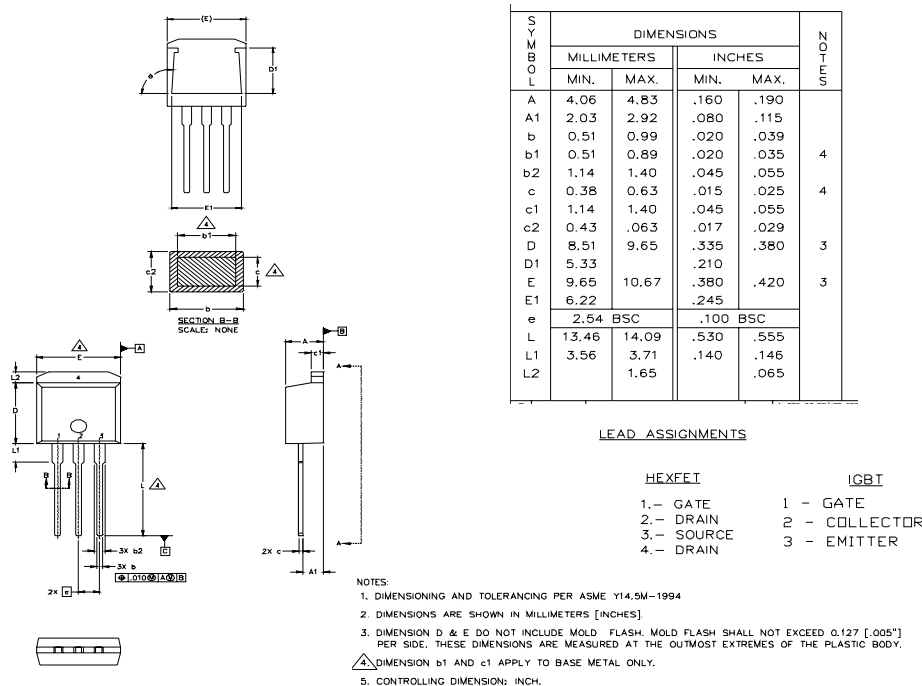
INTERNATIONAL
RECTIFIER
LOGO
ASSEMBLY
LOT CODE



PART NUMBER
DATE CODE
P = DESIGNATES LEAD-FREE
PRODUCT (OPTIONAL)
YEAR 0 = 2000
WEEK 02
A = ASSEMBLY SITE CODE

IRGB/S/SL4B60KD1PbF

TO-262 Package Outline

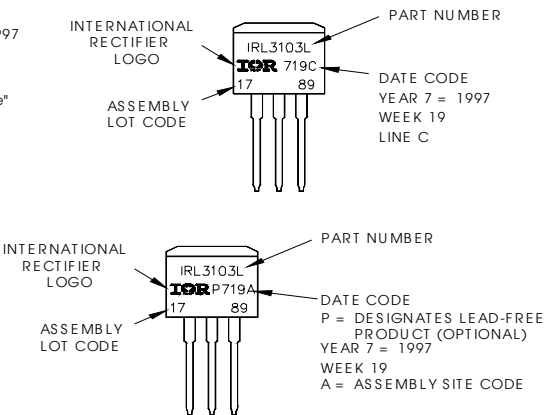


TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"

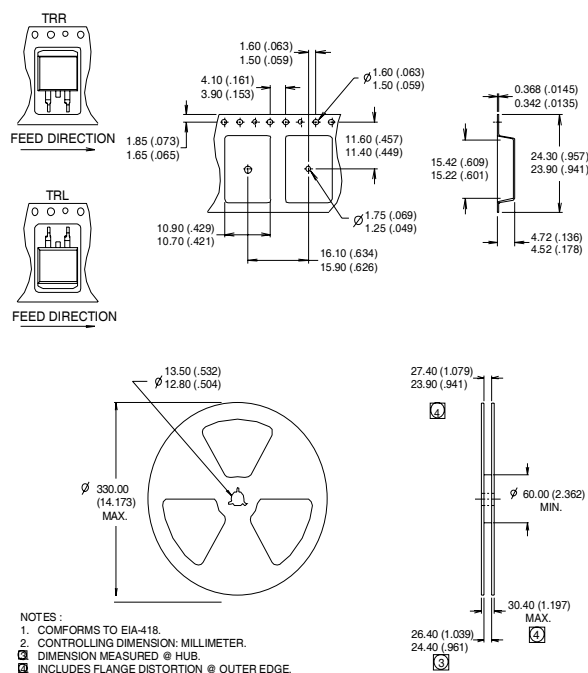
Note: "P" in assembly line position indicates "Lead-Free"

OR



IRGB/S/SL4B60KD1PbF

D²Pak Tape & Reel Information



Notes:

- ① $V_{CC} = 80\%$ (V_{CES}), $V_{GE} = 15V$, $L = 100\mu H$, $R_G = 100\Omega$.
- ② When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.
- ③ Energy losses include "tail" and diode reverse recovery, using Diode FD059H06A5.

TO-220AB package is not recommended for Surface Mount Application.

Data and specifications subject to change without notice.
This product has been designed and qualified for Industrial market.
Qualification Standards can be found on IR's Web site.

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105

TAC Fax: (310) 252-7903

Visit us at www.irf.com for sales contact information. 08/04